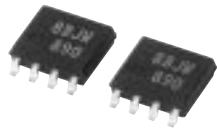


MITSUBISHI Pch POWER MOSFET

# FY8ABJ-03

HIGH-SPEED SWITCHING USE

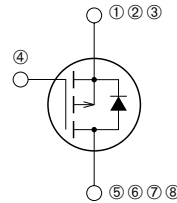
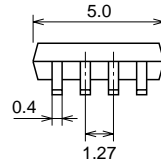
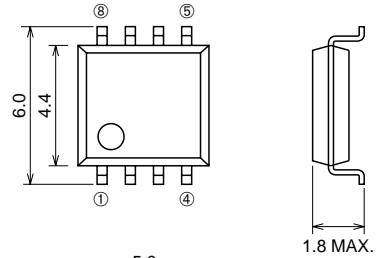
## FY8ABJ-03



- 4V DRIVE
- V<sub>DSS</sub> ..... -30V
- r<sub>DS (ON)</sub> (MAX) ..... 20mΩ
- I<sub>D</sub> ..... -8A

## OUTLINE DRAWING

Dimensions in mm



① ② ③ SOURCE  
④ GATE  
⑤ ⑥ ⑦ ⑧ DRAIN

SOP-8

## APPLICATION

Motor control, Lamp control, Solenoid control  
DC-DC converter, etc.

## MAXIMUM RATINGS (T<sub>c</sub> = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>DSS</sub>	Drain-source voltage	V <sub>GS</sub> = 0V	-30	V
V <sub>GSS</sub>	Gate-source voltage	V <sub>DS</sub> = 0V	±20	V
I <sub>D</sub>	Drain current		-8	A
I <sub>DM</sub>	Drain current (Pulsed)		-56	A
I <sub>DA</sub>	Avalanche drain current (Pulsed)	L = 10μH	-8	A
I <sub>S</sub>	Source current		-2.1	A
I <sub>SM</sub>	Source current (Pulsed)		-8.4	A
P <sub>D</sub>	Maximum power dissipation		2.0	W
T <sub>ch</sub>	Channel temperature		-55 ~ +150	°C
T <sub>stg</sub>	Storage temperature		-55 ~ +150	°C
—	Weight	Typical value	0.07	g

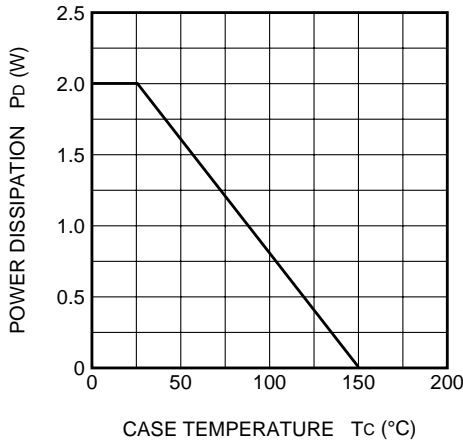
Sep.1998

**ELECTRICAL CHARACTERISTICS** (Tch = 25°C)

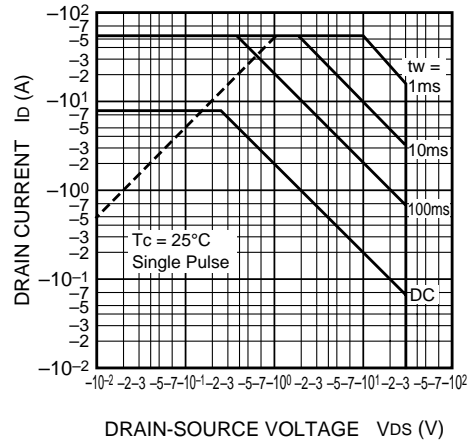
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V(BR)DSS	Drain-source breakdown voltage	Id = -1mA, VGS = 0V	-30	—	—	V
IGSS	Gate-source leakage current	VGS = ±20V, VDS = 0V	—	—	±0.1	μA
IDSS	Drain-source leakage current	VDS = -30V, VGS = 0V	—	—	-0.1	mA
VGS(th)	Gate-source threshold voltage	Id = -1mA, VDS = -10V	-1.5	-2.0	-2.5	V
rDS(ON)	Drain-source on-state resistance	Id = -8A, VGS = -10V	—	14	20	mΩ
rDS(ON)	Drain-source on-state resistance	Id = -4A, VGS = -4V	—	26	37	mΩ
VDS(ON)	Drain-source on-state voltage	Id = -8A, VGS = -10V	—	0.112	0.160	V
yfs	Forward transfer admittance	Id = -8A, VDS = -10V	—	19	—	S
Ciss	Input capacitance	VDS = -10V, VGS = 0V, f = 1MHz	—	3650	—	pF
Coss	Output capacitance		—	900	—	pF
Crss	Reverse transfer capacitance		—	385	—	pF
td(on)	Turn-on delay time	VDD = -15V, Id = -4A, VGS = -10V, RGEN = RGS = 50Ω	—	30	—	ns
tr	Rise time		—	55	—	ns
td(off)	Turn-off delay time		—	250	—	ns
tf	Fall time		—	105	—	ns
VSD	Source-drain voltage	IS = -2.1A, VGS = 0V	—	-0.77	-1.20	V
Rth(ch-a)	Thermal resistance	Channel to ambient	—	—	62.5	°C/W
trr	Reverse recovery time	IS = -2.1A, dis/dt = 50A/μs	—	100	—	ns

**PERFORMANCE CURVES**

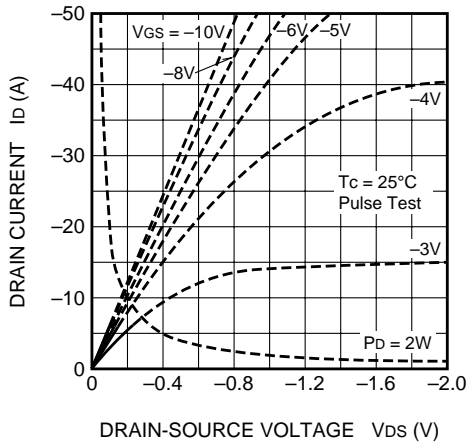
**POWER DISSIPATION DERATING CURVE**



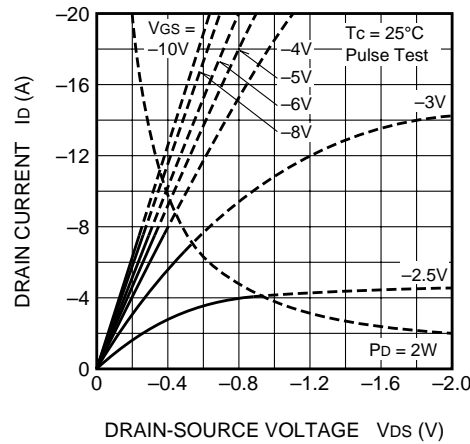
**MAXIMUM SAFE OPERATING AREA**

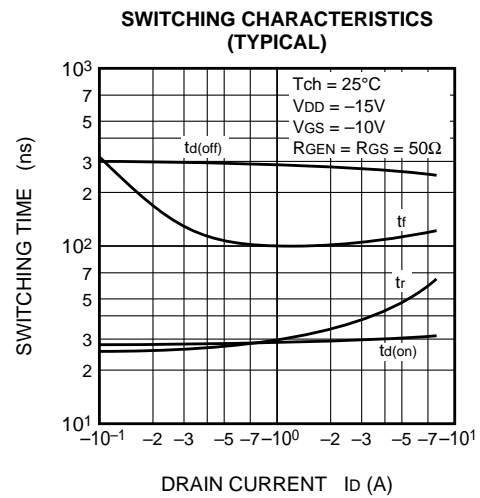
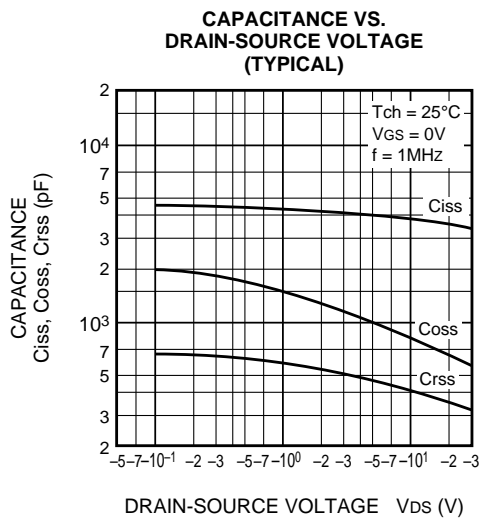
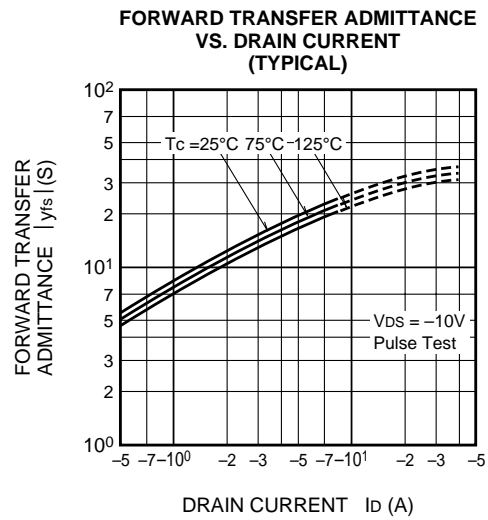
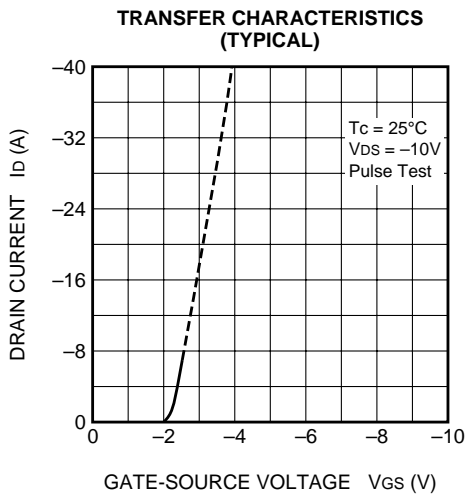
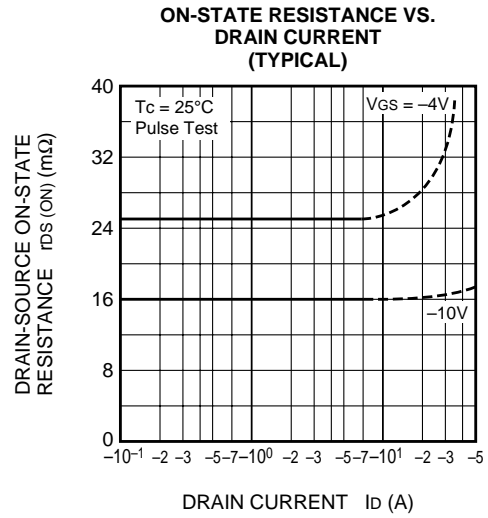
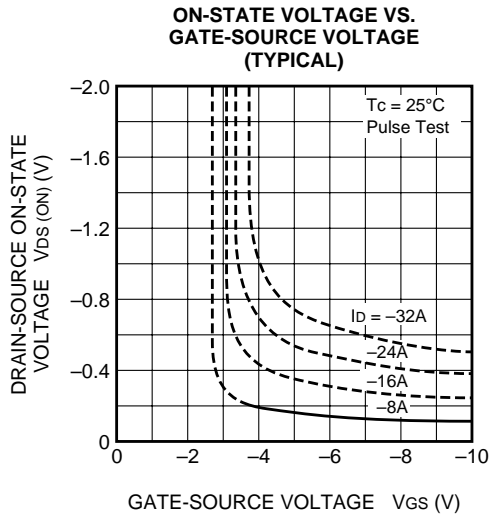


**OUTPUT CHARACTERISTICS (TYPICAL)**

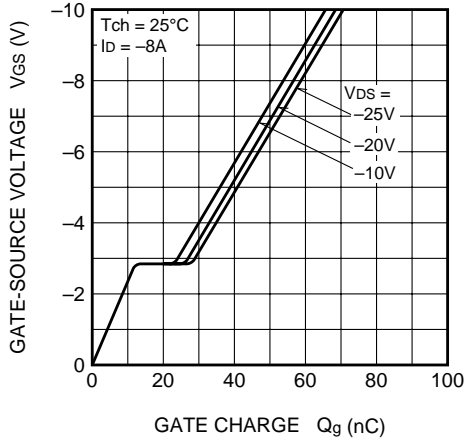


**OUTPUT CHARACTERISTICS (TYPICAL)**

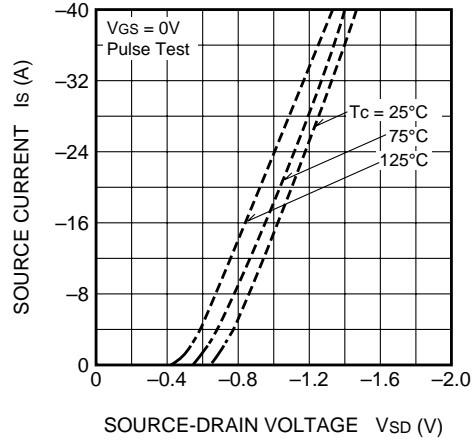




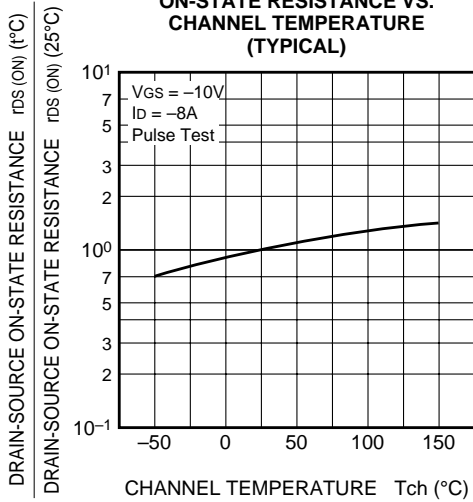
**GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)**



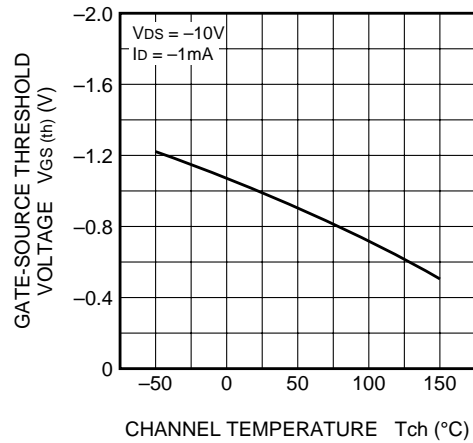
**SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)**



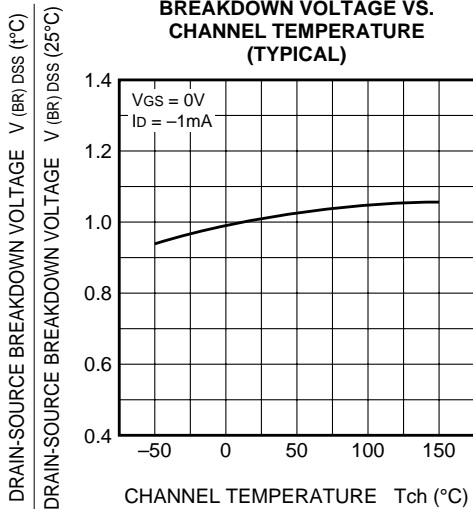
**ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)**



**THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)**



**BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS**

